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Defect engineering using microwave processing in SiC and GaAs

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Semiconductor Science and Technology
2022-07-01 | Journal article
DOI: 10.1088/1361-6641/ac6f17
CONTRIBUTORS: Oleg Olikh; Petro Lytvyn

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Estimation for iron contamination in Si solar cell by ideality factor: Deep neural network approach

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Progress in Photovoltaics: Research and Applications
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DOI: 10.1002/pip.3539
CONTRIBUTORS: Oleg Olikh; Oleg Lozitsky; Oleksii Zavhorodnii

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Intensification of iron–boron complex association in silicon solar cells under acoustic wave action

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Journal of Materials Science: Materials in Electronics
2022-06 | Journal article
DOI: 10.1007/s10854-022-08252-3
CONTRIBUTORS: Oleg Olikh; Vitaliy Kostylyov; Victor Vlasiuk; Roman Korkishko; Roman Chupryna

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Features of FeB pair light-induced dissociation and repair in silicon n+-p-p+ structures under ultrasound loading

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Journal of Applied Physics
2021-12-21 | Journal article
DOI: 10.1063/5.0073135
CONTRIBUTORS: O. Olikh; V. Kostylyov; V. Vlasiuk; R. Korkishko; Ya. Olikh; R. Chupryna

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Influence of γ-irradiation and ultrasound treatment on current mechanism in Au-SiO<inf>2</inf>-Si structure

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Solid-State Electronics
2020 | Journal article
DOI: 10.1016/j.sse.2019.107712
EID: 2-s2.0-85076863216
Part of ISBN: 00381101
CONTRIBUTORS: Gorb, A.M.; Korotchenkov, O.A.; Olikh, O.Y.; Podolian, A.O.; Chupryna, R.G.

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Mechanisms of Two-Stage Conductivity Relaxation in CdTe:Cl with Ultrasound

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Journal of Electronic Materials
2020 | Journal article
DOI: 10.1007/s11664-020-08179-7
EID: 2-s2.0-85084966084
Part of ISBN: 1543186X 03615235
CONTRIBUTORS: Olikh, Y.; Tymochko, M.; Olikh, O.

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Modeling of ideality factor value in n+--p--p+-Si structure Everyone

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2020 | Journal article
DOI: 10.30970/jps.24.4701
CONTRIBUTORS: O. Ya. Olikh; O. V. Zavhorodnii

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Relationship between the ideality factor and the iron concentration in silicon solar cells Everyone

Superlattices and Microstructures
2019 | Journal article
DOI: 10.1016/j.spmi.2019.106309
EID: 2-s2.0-85073691419
Part of ISBN: 10963677 07496036
CONTRIBUTORS: Olikh, O.Y.

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Clusters of Point Defects Near Dislocations as a Tool to Control CdZnTe Electrical Parameters by Ultrasound Everyone

Journal of Electronic Materials
2018 | Journal article
DOI: 10.1007/s11664-018-6332-4
EID: 2-s2.0-85046885305
Part of ISBN: 03615235
CONTRIBUTORS: Olikh, Y.M.; Tymochko, M.D.; Olikh, O.Y.; Shenderovsky, V.A.

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Acoustically driven degradation in single crystalline silicon solar cell Everyone

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2018-05 | Journal article
DOI: 10.1016/j.spmi.2018.03.027
CONTRIBUTORS: O.Ya. Olikh

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Acousto–defect interaction in irradiated and non-irradiated silicon n+–p structures Everyone

Journal of Applied Physics
2018-04-28 | Journal article
DOI: 10.1063/1.5001123
CONTRIBUTORS: O. Ya. Olikh; A. M. Gorb; R. G. Chupryna; O. V. Pristay-Fenenkov

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Effect of ultrasound on reverse leakage current of silicon Schottky barrier structure Everyone

Journal of Semiconductors
2016 | Journal article
DOI: 10.1088/1674-4926/37/12/122002
EID: 2-s2.0-84999801366
Part of ISBN: 16744926
CONTRIBUTORS: Ya Olikh, O.; Voitenko, K.V.; Burbelo, R.M.; Olikh, Ja.M.

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On the mechanism of ultrasonic loading effect in silicon-based Schottky diodes Everyone

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2016 | Journal article
DOI: 10.1016/j.ultras.2015.12.001
EID: 2-s2.0-84953432942
Part of ISBN: 0041624X
CONTRIBUTORS: Olikh, O.; Voytenko, K.

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Reversible influence of ultrasound on γ-irradiated Mo/n-Si Schottky barrier structure Everyone

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DOI: 10.1016/j.ultras.2014.10.008
EID: 2-s2.0-84911976170
Part of ISBN: 0041624X

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CONTRIBUTORS: Olikh, O.Y.

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Review and test of methods for determination of the Schottky diode parameters Everyone

Journal of Applied Physics
2015 | Journal article
DOI: 10.1063/1.4926420
EID: 2-s2.0-84953923466
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CONTRIBUTORS: Olikh, O.Y.

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Ultrasound influence on I-V-T characteristics of silicon Schottky barrier structure Everyone

Journal of Applied Physics
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DOI: 10.1063/1.4906844
EID: 2-s2.0-84923666777
Part of ISBN: 10897550 00218979
CONTRIBUTORS: Olikh, O.Ya.; Voytenko, K.V.; Burbelo, R.M.

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FEATURES OF ULTRASOUND ABSORPTION BY DISLOCATIONS IN SUBGRAIN-FREE Cd0.2Hg0.8Te CRYSTALS Everyone

Ukrainian Journal of Physics
2014 | Journal article
DOI: 10.15407/UJPE59.01.0050
WOSUID: WOS:000422067200006
CONTRIBUTORS: Lysyuk, I. O.; Olikh, Ya. M.; Olikh, O. Ya.; Beketov, G. V.

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Ukrainian Journal of Physics
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EID: 2-s2.0-84892965065
Part of ISBN: 20710194 20710186
CONTRIBUTORS: Lysyuk, I.O.; Olikh, Y.M.; Olikh, O.Y.; Beketov, G.V.

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Effect of ultrasonic loading on current in Mo/n-n⁺-Si with Schottky barriers Everyone

Semiconductors
2013 | Journal article
DOI: 10.1134/S106378261307018X
EID: 2-s2.0-84879804840
Part of ISBN: 10637826
CONTRIBUTORS: Olikh, O.Y.

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Features of charge transport in Mo/n-Si structures with a Schottky barrier Everyone

Ukrainian Journal of Physics
2013 | Journal article
DOI: 10.15407/ujpe58.02.0126
EID: 2-s2.0-84874328147
Part of ISBN: 20710194 20710186
CONTRIBUTORS: Olikh, O.Y.

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Non-monotonic γ-ray influence on Mo/n-Si schottky barrier structure properties Everyone

IEEE Transactions on Nuclear Science
2013 | Journal article
DOI: 10.1109/TNS.2012.2234137
EID: 2-s2.0-84873715135
Part of ISBN: 00189499
CONTRIBUTORS: Olikh, O.Y.

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Features of dynamic acoustically induced modification of photovoltaic parameters of silicon solar cells Everyone

Semiconductors
2011 | Journal article
DOI: 10.1134/S1063782611060170
EID: 2-s2.0-84886943248
Part of ISBN: 10637826
CONTRIBUTORS: Olikh, O.Y.

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Features of neutron irradiation effect on dynamic acousto-defect interaction in silicon solar cells

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Ukrainian Journal of Physics
2010 | Journal article
EID: 2-s2.0-77955875982
Part of ISBN: 20710194 20710186
CONTRIBUTORS: Olikh, O.Y.

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FEATURES OF NEUTRON IRRADIATION EFFECT ON DYNAMIC ACOUSTO-DEFECT INTERACTION IN SILICON SOLAR CELLS

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Ukrainian Journal of Physics
2010 | Journal article
WOSUID: WOS:000421986600003
CONTRIBUTORS: Olikh, O. Ya.

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Ultrasonic assisted nanomanipulations with atomic force microscope

Everyone

Semiconductor Physics Quantum Electronics & Optoelectronics
2010 | Journal article
DOI: 10.15407/SPQEO13.01.036
WOSUID: WOS:000451133900007
CONTRIBUTORS: Lytvyn, P. M.; Olikh, O. Ya.; Lytvyn, O. S.; Dyachyns'ka, O. M.; Prokopenko, I. V.

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Ultrasonically recovered performance of γ-Irradiated metal-silicon structures

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IEEE Transactions on Nuclear Science
2010 | Journal article
DOI: 10.1109/TNS.2010.2047655
EID: 2-s2.0-77953723251
Part of ISBN: 00189499
CONTRIBUTORS: Gorb, A.M.; Korotchenkov, O.A.; Olikh, O.Y.; Podolian, A.O.

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The variation in activity of recombination centers in silicon p-n structures under the conditions of acoustic loading

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Semiconductors
2009 | Journal article
DOI: 10.1134/S1063782609060116
EID: 2-s2.0-84886943256
Part of ISBN: 10637826
CONTRIBUTORS: Olikh, O.Ya.

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The dynamic ultrasound influence on the diffusion and drift of the charge carriers in silion p-n structures

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Materials Research Society Symposium - Proceedings
2007 | Journal article
WOSUID: WOS:000250474700039
CONTRIBUTORS: Burbelo, Roman M.; Olikh, Oleg Y.; Hinders, Mark K.

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Source: Web of Science Researcher Profile Sync

The dynamic ultrasound influence on the diffusion and drift of the charge carriers in silion p-n structures

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Materials Research Society Symposium Proceedings
2007 | Conference paper
EID: 2-s2.0-45749113702
Part of ISBN: 02729172
CONTRIBUTORS: Burbelo, R.M.; Olikh, O.Y.; Hinders, M.K.

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Source: Oleg Olikh *via* Scopus - Elsevier

Acoustic wave corrected current-voltage characteristics of GaAs-based structures with Schottky contacts

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Technical Physics Letters
2006 | Journal article
DOI: 10.1134/S1063785006060204
EID: 2-s2.0-33745577187
Part of ISBN: 10637850
CONTRIBUTORS: Olikh, O.Ya.; Pinchuk, T.N.

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Ultrasound-stimulated increase in the electron diffusion length in p-Si crystals

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Physics of the Solid State
2002 | Journal article
DOI: 10.1134/1.1494617
EID: 2-s2.0-0036024463
Part of ISBN: 10637834
CONTRIBUTORS: Olikh, O.Ya.; Ostrovskii, I.V.

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Acoustically driven optical phenomena in bulk and low-dimensional semiconductors

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Journal of Optics A: Pure and Applied Optics
2001 | Journal article
DOI: 10.1088/1464-4258/3/4/364
EID: 2-s2.0-0035391613
Part of ISBN: 14644258
CONTRIBUTORS: Ostrovskii, I.V.; Korotchenkov, O.A.; Ya Olikh, O.; Podolyan, A.A.; Chupryna, R.G.; Torres-Cisneros, M.

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Ultrasonic influence on point defects in a dislocation free Si

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IEEE ULTRASONICS SYMPOSIUM PROCEEDINGS, VOLS 1-3
2000 | Conference paper

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DOI: 10.1109/ULTSYM.2000.922602
WOSUID: WOS:000171881300108
CONTRIBUTORS: Ostrovskii, IV; Olikh, OJ; Nadtochii, AB

Source: Web of Science Researcher Profile Sync

Ultrasonic influence on point defects in a dislocation free Si

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Proceedings of the IEEE Ultrasonics Symposium
2000 | Conference paper
EID: 2-s2.0-0034579992
Part of ISBN: 10510117
CONTRIBUTORS: Ostrovskii, I.V.; Olikh, O.Ja.; Nadtochii, A.B.

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Source: Oleg Olikh *via* Scopus - Elsevier

Characterization of interface deep levels in as vapor grown EPI-GaAs

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Solid State Communications
1998 | Journal article
DOI: 10.1016/S0038-1098(98)00236-1
EID: 2-s2.0-0032499858
Part of ISBN: 00381098
CONTRIBUTORS: Ostrovskii, I.V.; Olikh, O.Ya.

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